

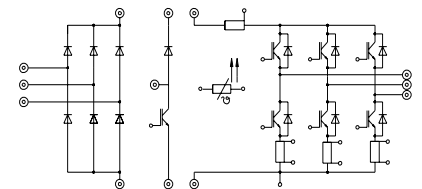
SKiiP 22 NAB 12 - SKiiP 22 NAB 12 I

Absolute Maximum Ratings		Values	Units
Symbol	Conditions ¹⁾		
Inverter & Chopper			
V_{CES}		1200	V
V_{GES}		± 20	V
I_C	$T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	23 / 15	A
I_{CM}	$t_p < 1 \text{ ms}; T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	46 / 30	A
$I_F = -I_C$	$T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	24 / 17	A
$I_{FM} = -I_{CM}$	$t_p < 1 \text{ ms}; T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	48 / 34	A
Bridge Rectifier			
V_{RRM}		1500	V
I_D	$T_{\text{heatsink}} = 80 \text{ }^\circ\text{C}$	25	A
I_{FSM}	$t_p = 10 \text{ ms}; \sin. 180^\circ, T_j = 25 \text{ }^\circ\text{C}$	700	A
I^2t	$t_p = 10 \text{ ms}; \sin. 180^\circ, T_j = 25 \text{ }^\circ\text{C}$	2400	A ² s
T_j		- 40 ... + 150	$^\circ\text{C}$
T_{stg}		- 40 ... + 125	$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		min.	typ.	max.	Units
Symbol	Conditions ¹⁾				
IGBT - Inverter & Chopper					
V_{CESat}	$I_C = 15 \text{ A}, T_j = 25 (125) \text{ }^\circ\text{C}$	-	2,5(3,1)	3,0(3,7)	V
$t_{d(on)}$	$V_{CC} = 600 \text{ V}; V_{GE} = \pm 15 \text{ V}$	-	55	110	ns
t_r	$I_C = 15 \text{ A}; T_j = 125 \text{ }^\circ\text{C}$	-	45	90	ns
$t_{d(off)}$	$R_{gon} = R_{goff} = 82 \text{ } \Omega$	-	400	600	ns
t_f	inductive load	-	70	100	ns
$E_{on} + E_{off}$		-	4,0	-	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}, 1 \text{ MHz}$	-	1,0	-	nF
R_{thjh}	per IGBT	-	-	1,4	K/W
Diode ²⁾ - Inverter & Chopper					
$V_F = V_{EC}$	$I_F = 15 \text{ A}, T_j = 25 (125) \text{ }^\circ\text{C}$	-	2,0(1,8)	2,5(2,3)	V
V_{TO}	$T_j = 125 \text{ }^\circ\text{C}$	-	1,0	1,2	V
r_T	$T_j = 125 \text{ }^\circ\text{C}$	-	53	73	m Ω
I_{RRM}	$I_F = 15 \text{ A}, V_R = - 600 \text{ V}$	-	16	-	A
Q_{rr}	$di_F/dt = - 400 \text{ A}/\mu\text{s}$	-	2,7	-	μC
E_{off}	$V_{GE} = 0 \text{ V}, T_j = 125 \text{ }^\circ\text{C}$	-	0,6	-	mJ
R_{thjh}	per diode	-	-	1,7	K/W
Diode - Rectifier					
V_F	$I_F = 35 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$	-	1,2	-	V
R_{thjh}	per diode	-	-	1,6	K/W
Temperature Sensor					
R_{TS}	$T = 25 / 100 \text{ }^\circ\text{C}$		1000 / 1670		Ω
Shunts (SKiiP 22 NAB 12 I)					
$R_{cs(dc)}$	5 % ⁴⁾		16,5		m Ω
$R_{cs(ac)}$	1 %		10		m Ω
Mechanical Data					
M_1	case to heatsink, SI Units	2	-	2,5	Nm
Case	mechanical outline see page B 16 - 8		M2		

MiniSKiiP 2 SEMIKRON integrated intelligent Power SKiiP 22 NAB 12 SKiiP 22 NAB 12 I ³⁾ 3-phase bridge rectifier + braking chopper + 3-phase bridge inverter

Case M2



UL recognized file no. E63532

- specification of shunts and temperature sensor see part A
- common characteristics see page B 16 - 4

- ¹⁾ $T_{\text{heatsink}} = 25 \text{ }^\circ\text{C}$, unless otherwise specified
- ²⁾ CAL = Controlled Axial Lifetime Technology (soft and fast recovery)
- ³⁾ With integrated DC and/or AC shunts
- ⁴⁾ accuracy of pure shunt, please note that for DC shunt no separate sensing contact is used.

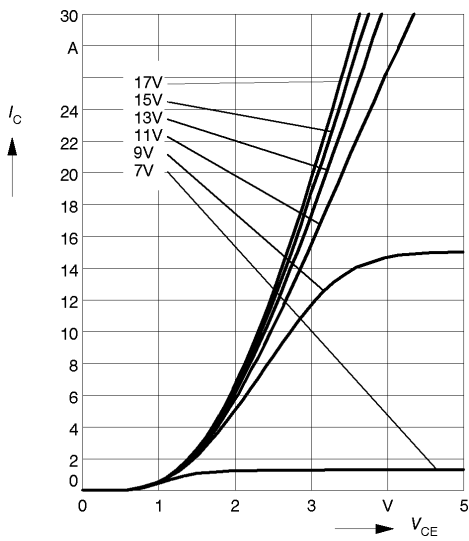


Fig. 1 Typ. output characteristic, $t_p = 80 \mu s$; $25 \text{ }^\circ\text{C}$

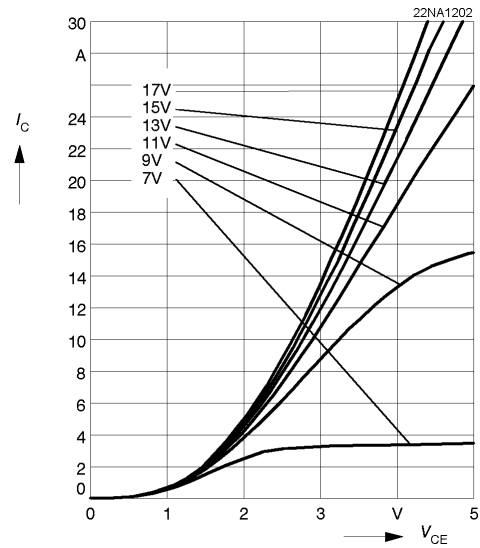


Fig. 2 Typ. output characteristic, $t_p = 80 \mu s$; $125 \text{ }^\circ\text{C}$

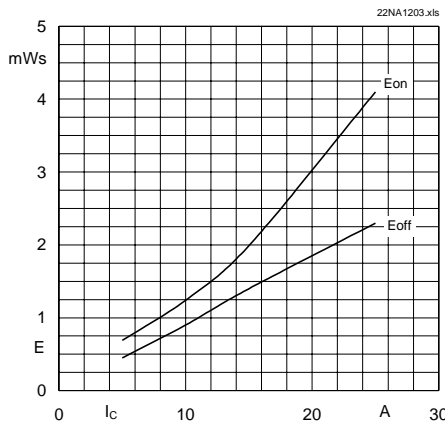


Fig. 3 Turn-on /-off energy = $f(I_C)$

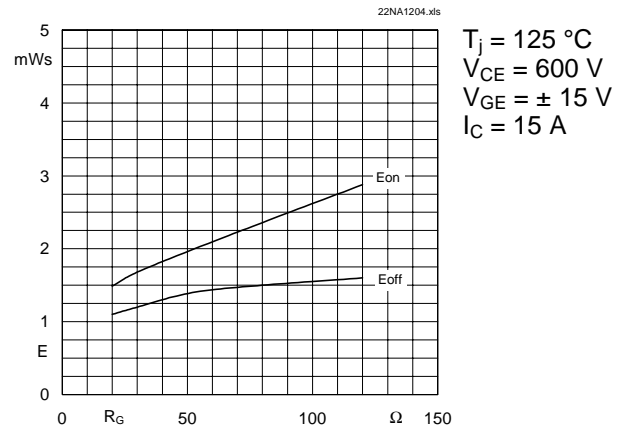


Fig. 4 Turn-on /-off energy = $f(R_G)$

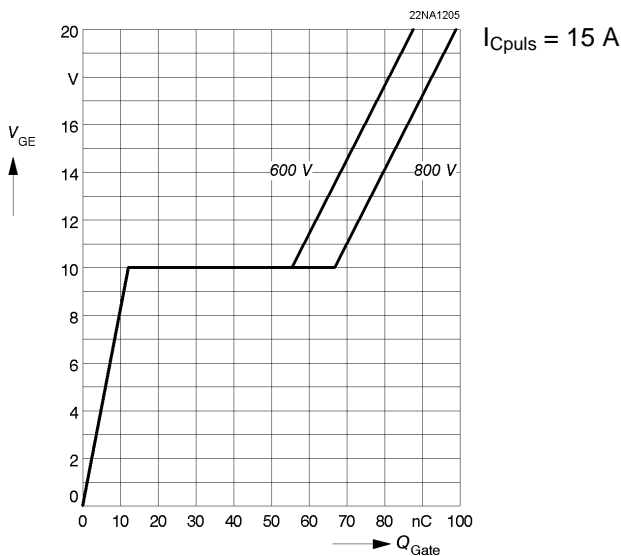


Fig. 5 Typ. gate charge characteristic

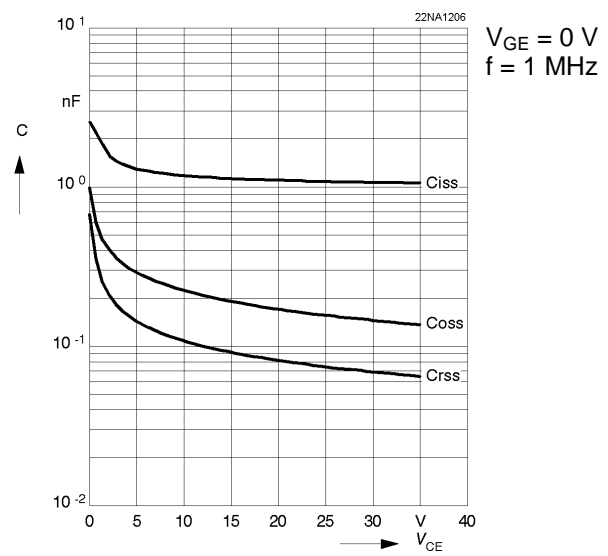


Fig. 6 Typ. capacitances vs. V_{CE}

MiniSKiiP 1200 V

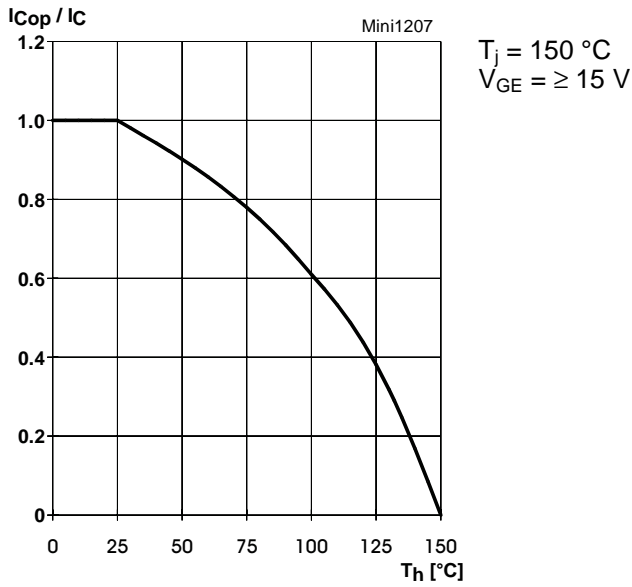


Fig. 7 Rated current of the IGBT $I_{COp} / I_C = f(T_h)$

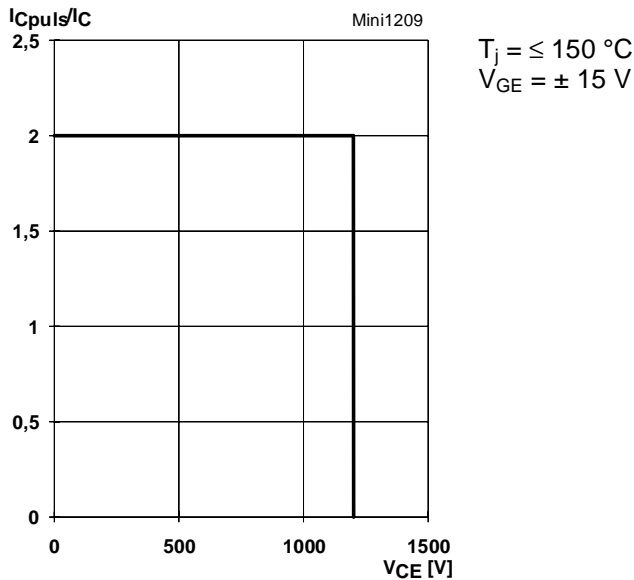


Fig. 9 Turn-off safe operating area (RBSOA) of the IGBT



Fig. 10 Safe operating area at short circuit of the IGBT

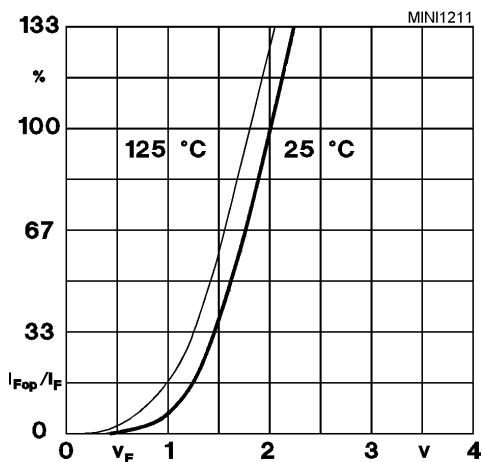


Fig. 11 Typ. freewheeling diode forward characteristic

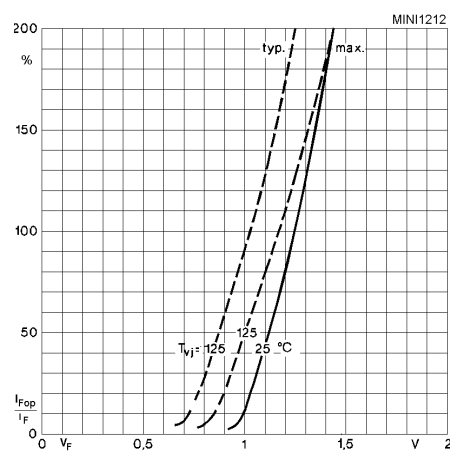


Fig. 12 Forward characteristic of the input bridge diode

